

# PHP3055E

## N-channel TrenchMOS standard level FET

Rev. 07 — 26 February 2010

Product data sheet

## 1. Product profile

### 1.1 General description

Standard level N-channel enhancement mode Field-Effect Transistor (FET) in a plastic package using TrenchMOS technology. This product is designed and qualified for use in computing, communications, consumer and industrial applications only.

### 1.2 Features and benefits

- Low conduction losses due to low on-state resistance
- Suitable for high frequency applications due to fast switching characteristics

### 1.3 Applications

- DC-to-DC convertors
- Switched-mode power supplies

### 1.4 Quick reference data

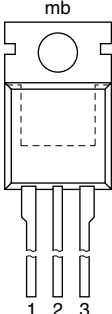
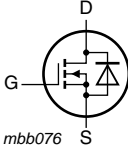
Table 1. Quick reference

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	-	60	V
$I_D$	drain current	$T_{mb} = 25\text{ °C}$ ; $V_{GS} = 10\text{ V}$ ; see <a href="#">Figure 1</a> and <a href="#">3</a>	-	-	10.3	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	-	33	W
<b>Dynamic characteristics</b>						
$Q_{GD}$	gate-drain charge	$V_{GS} = 10\text{ V}$ ; $I_D = 10\text{ A}$ ; $V_{DS} = 44\text{ V}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 12</a>	-	3.2	-	nC
<b>Static characteristics</b>						
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10\text{ V}$ ; $I_D = 5.5\text{ A}$ ; $T_j = 25\text{ °C}$ ; see <a href="#">Figure 10</a> and <a href="#">11</a>	-	120	150	m $\Omega$



## 2. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate		
2	D	drain		
3	S	source		
mb	D	mounting base; connected to drain		

**SOT78 (TO-220AB)**

## 3. Ordering information

Table 3. Ordering information

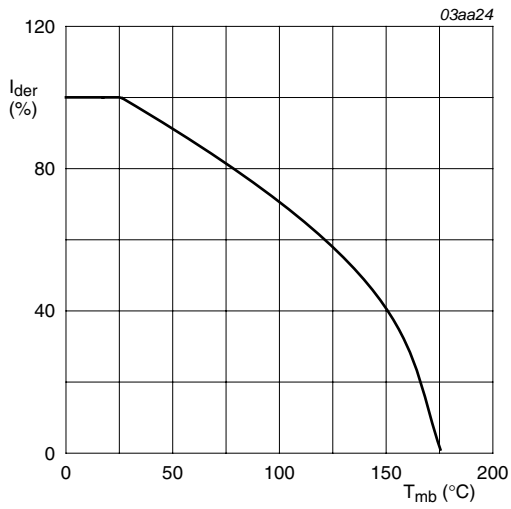
Type number	Package		Version
	Name	Description	
PHP3055E	TO-220AB	plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB	SOT78

## 4. Limiting values

**Table 4. Limiting values**

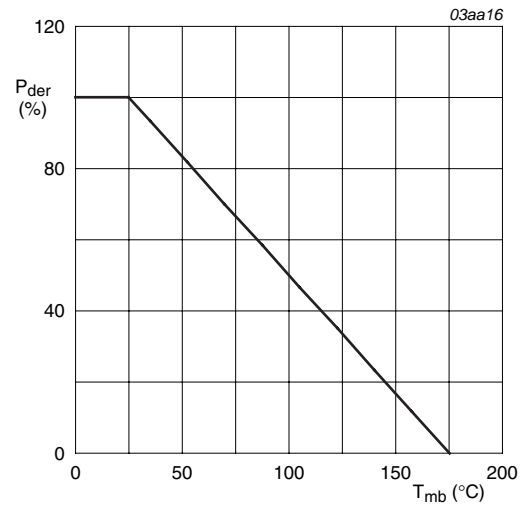
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
$V_{DS}$	drain-source voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$	-	60	V
$V_{DGR}$	drain-gate voltage	$T_j \geq 25\text{ °C}$ ; $T_j \leq 175\text{ °C}$ ; $R_{GS} = 20\text{ k}\Omega$	-	60	V
$V_{GS}$	gate-source voltage		-20	20	V
$I_D$	drain current	$V_{GS} = 10\text{ V}$ ; $T_{mb} = 100\text{ °C}$ ; see <a href="#">Figure 1</a>	-	7.3	A
		$V_{GS} = 10\text{ V}$ ; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 1</a> and <a href="#">3</a>	-	10.3	A
$I_{DM}$	peak drain current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 3</a>	-	41	A
$P_{tot}$	total power dissipation	$T_{mb} = 25\text{ °C}$ ; see <a href="#">Figure 2</a>	-	33	W
$T_{stg}$	storage temperature		-55	175	°C
$T_j$	junction temperature		-55	175	°C
<b>Source-drain diode</b>					
$I_S$	source current	$T_{mb} = 25\text{ °C}$	-	10.3	A
$I_{SM}$	peak source current	$t_p \leq 10\text{ }\mu\text{s}$ ; pulsed; $T_{mb} = 25\text{ °C}$	-	41	A
<b>Avalanche ruggedness</b>					
$E_{DS(AL)S}$	non-repetitive drain-source avalanche energy	$V_{GS} = 10\text{ V}$ ; $T_{j(init)} = 25\text{ °C}$ ; $I_D = 3.3\text{ A}$ ; $V_{sup} \leq 25\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; unclamped; $t_p = 0.22\text{ ms}$	-	25	mJ
$I_{DS(AL)S}$	non-repetitive drain-source avalanche current	$V_{GS} = 10\text{ V}$ ; $V_{sup} \leq 25\text{ V}$ ; $R_{GS} = 50\text{ }\Omega$ ; $T_{j(init)} = 25\text{ °C}$ ; unclamped; see <a href="#">Figure 4</a>	-	10.3	A



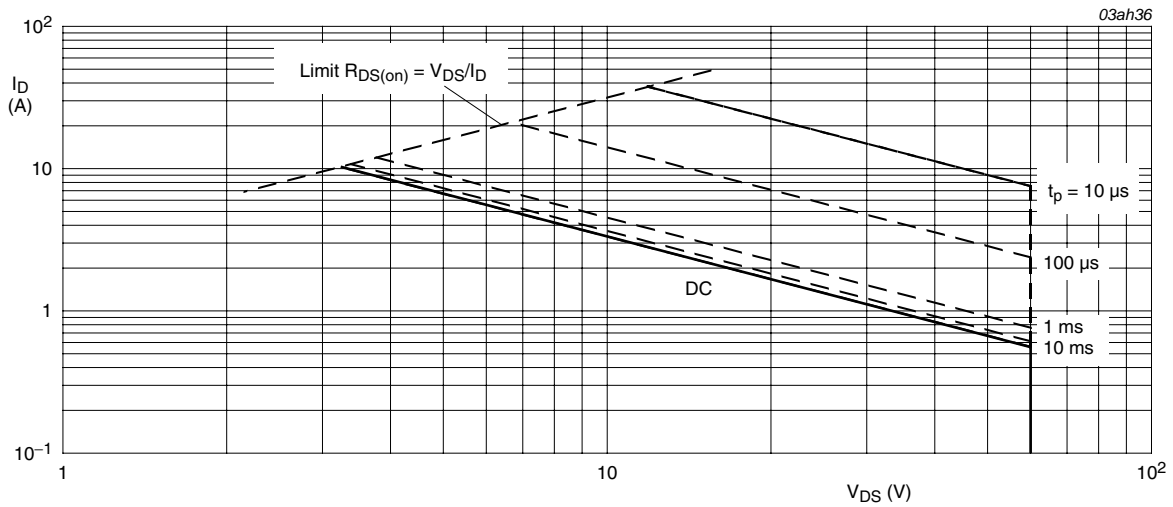
$$I_{der} = \frac{I_D}{I_{D(25^\circ\text{C})}} \times 100\%$$

Fig 1. Normalized continuous drain current as a function of mounting base temperature



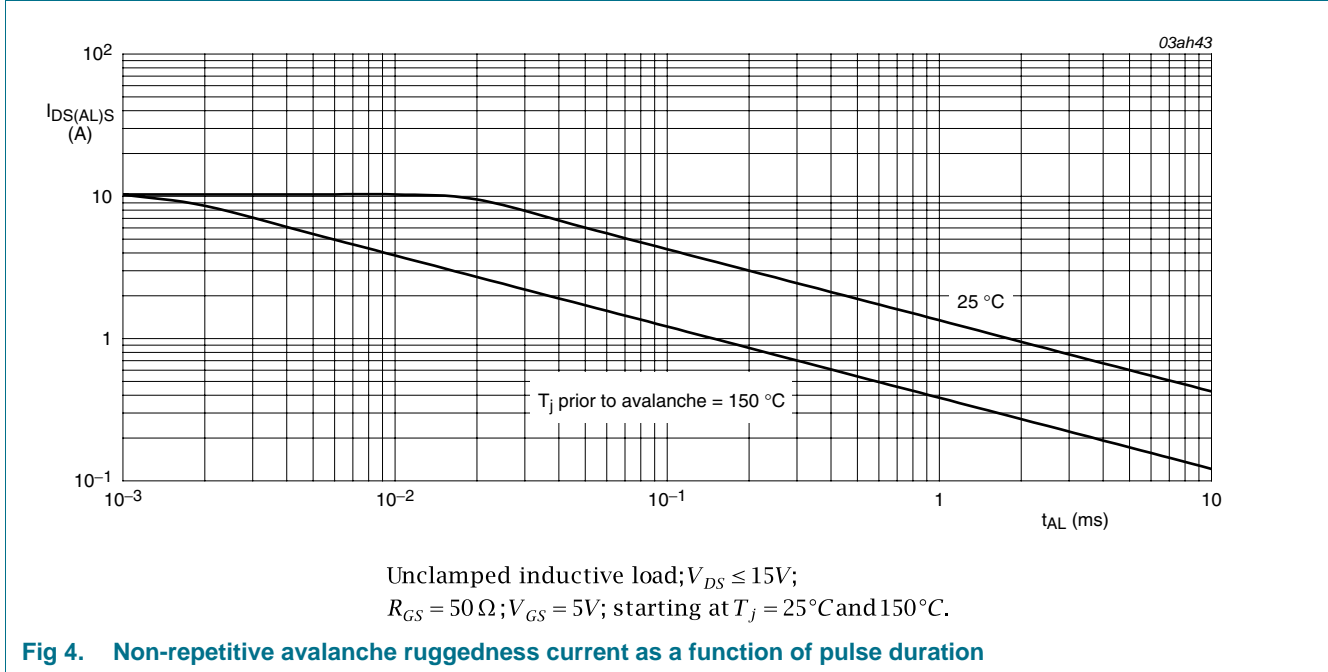
$$P_{der} = \frac{P_{tot}}{P_{tot(25^\circ\text{C})}} \times 100\%$$

Fig 2. Normalized total power dissipation as a function of mounting base temperature



$T_{mb} = 25^\circ\text{C}; I_{DM}$  is single pulse

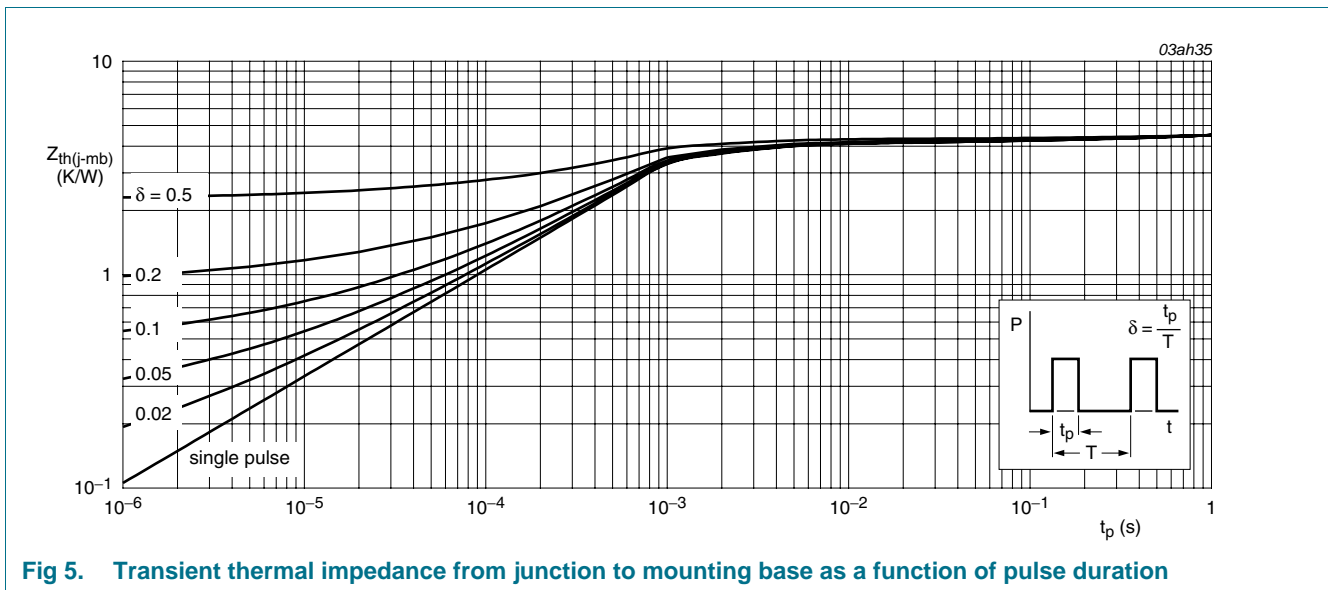
Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage



## 5. Thermal characteristics

Table 5. Thermal characteristics

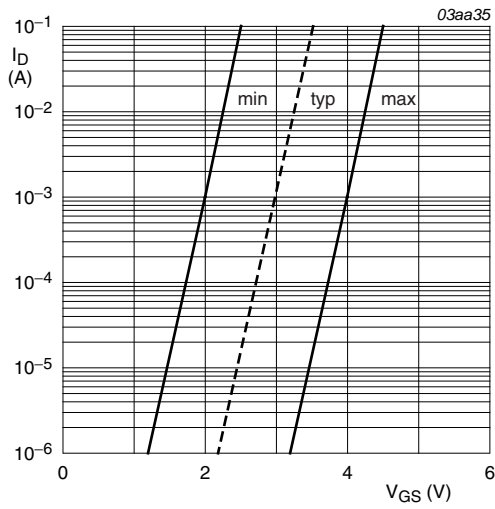
Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-mb)}$	thermal resistance from junction to mounting base	see <a href="#">Figure 5</a>	-	-	4.5	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	vertical in still air	-	60	-	K/W



## 6. Characteristics

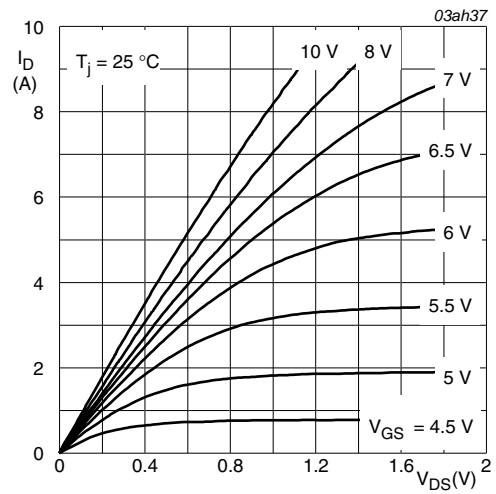
Table 6. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
<b>Static characteristics</b>						
$V_{(BR)DSS}$	drain-source breakdown voltage	$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = -55 \text{ }^\circ\text{C}$	55	-	-	V
		$I_D = 0.25 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	60	-	-	V
$V_{GS(th)}$	gate-source threshold voltage	$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a>	1	-	-	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = -55 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a>	-	-	6	V
		$I_D = 1 \text{ mA}; V_{DS} = V_{GS}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 9</a>	2	3	4	V
$I_{DSS}$	drain leakage current	$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 175 \text{ }^\circ\text{C}$	-	-	500	$\mu\text{A}$
		$V_{DS} = 55 \text{ V}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	0.05	10	$\mu\text{A}$
$I_{GSS}$	gate leakage current	$V_{GS} = 10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
		$V_{GS} = -10 \text{ V}; V_{DS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	10	100	nA
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 10 \text{ V}; I_D = 5.5 \text{ A}; T_j = 175 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a> and <a href="#">11</a>	-	250	315	m $\Omega$
		$V_{GS} = 10 \text{ V}; I_D = 5.5 \text{ A}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 10</a> and <a href="#">11</a>	-	120	150	m $\Omega$
<b>Dynamic characteristics</b>						
$Q_{G(tot)}$	total gate charge	$I_D = 10 \text{ A}; V_{DS} = 44 \text{ V}; V_{GS} = 10 \text{ V};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 12</a>	-	5.8	-	nC
$Q_{GS}$	gate-source charge		-	1.5	-	nC
$Q_{GD}$	gate-drain charge		-	3.2	-	nC
$C_{iss}$	input capacitance	$V_{DS} = 25 \text{ V}; V_{GS} = 0 \text{ V}; f = 1 \text{ MHz};$ $T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 13</a>	-	190	250	pF
$C_{oss}$	output capacitance		-	55	80	pF
$C_{rss}$	reverse transfer capacitance		-	40	50	pF
$t_{d(on)}$	turn-on delay time	$V_{DS} = 30 \text{ V}; R_L = 2.7 \text{ } \Omega; V_{GS} = 10 \text{ V};$ $R_{G(ext)} = 5.6 \text{ } \Omega; T_j = 25 \text{ }^\circ\text{C}$	-	3	10	ns
$t_r$	rise time		-	26	35	ns
$t_{d(off)}$	turn-off delay time		-	8	15	ns
$t_f$	fall time		-	10	20	ns
<b>Source-drain diode</b>						
$V_{SD}$	source-drain voltage	$I_S = 10 \text{ A}; V_{GS} = 0 \text{ V}; T_j = 25 \text{ }^\circ\text{C};$ see <a href="#">Figure 14</a>	-	1.1	1.5	V
$t_{rr}$	reverse recovery time	$I_S = 10 \text{ A}; dI_S/dt = -100 \text{ A}/\mu\text{s}; V_{GS} = 0 \text{ V};$ $V_{DS} = 25 \text{ V}; T_j = 25 \text{ }^\circ\text{C}$	-	32	-	ns
$Q_r$	recovered charge		-	50	-	nC



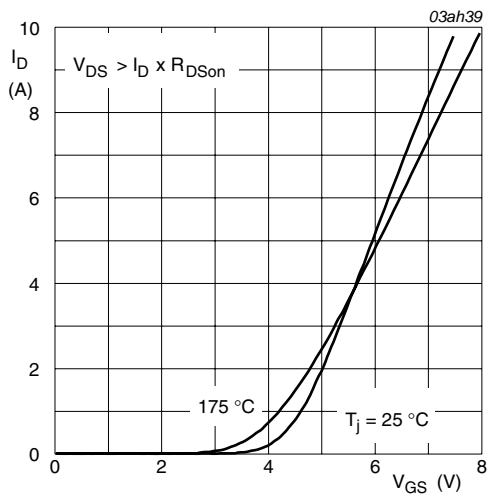
$T_j = 25^\circ\text{C}; V_{DS} = 5\text{V}$

**Fig 6. Sub-threshold drain current as a function of gate-source voltage**



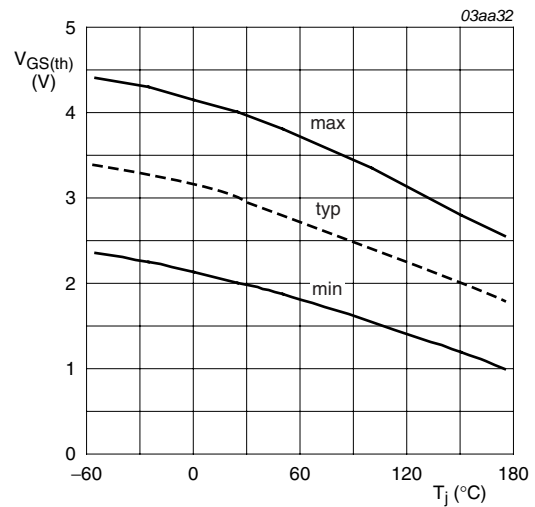
$T_j = 25^\circ\text{C}$

**Fig 7. Output characteristics: drain current as a function of drain-source voltage; typical values**



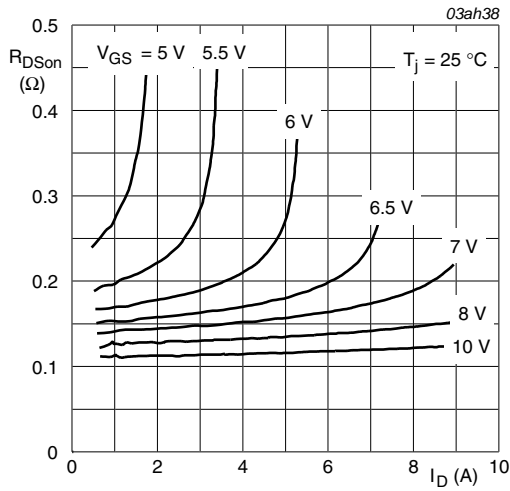
$T_j = 25^\circ\text{C}$  and  $175^\circ\text{C}; V_{DS} > I_D \times R_{DSon}$

**Fig 8. Transfer characteristics: drain current as a function of gate-source voltage; typical values**



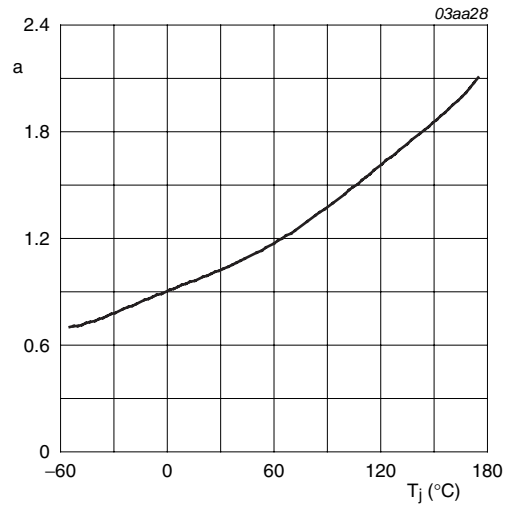
$I_D = 1\text{mA}; V_{DS} = V_{GS}$

**Fig 9. Gate-source threshold voltage as a function of junction temperature**



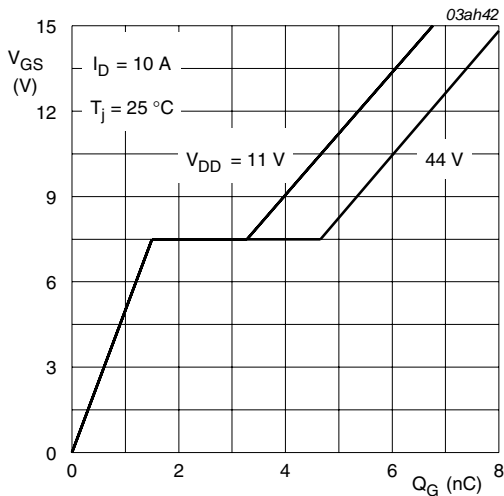
$T_j = 25^\circ C$

Fig 10. Drain-source on-state resistance as a function of drain current; typical values



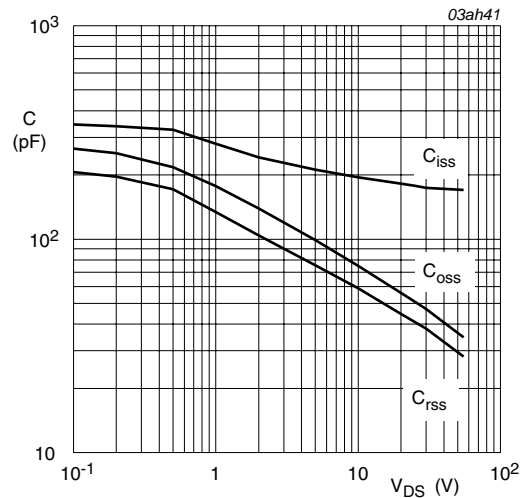
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ C)}}$$

Fig 11. Normalized drain-source on-state resistance factor as a function of junction temperature



$I_D = 10A; V_{DD} = 11V$  and  $44V$

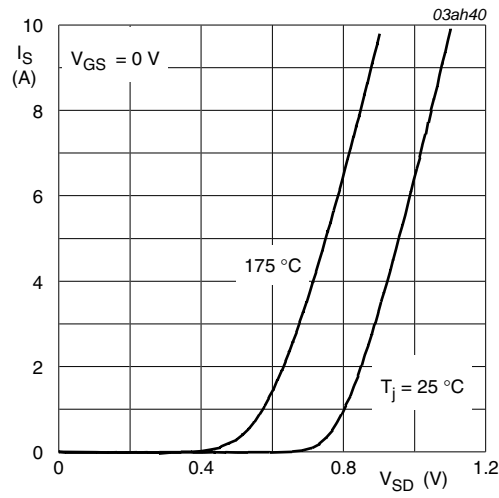
Fig 12. Gate-source voltage as a function of gate charge; typical values



$V_{GS} = 0V; f = 1MHz$

Fig 13. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values





$T_j = 25^\circ C$  and  $175^\circ C$ ;  $V_{GS} = 0V$

Fig 14. Source current as a function of source-drain voltage; typical values

7. Package outline

Plastic single-ended package; heatsink mounted; 1 mounting hole; 3-lead TO-220AB

SOT78

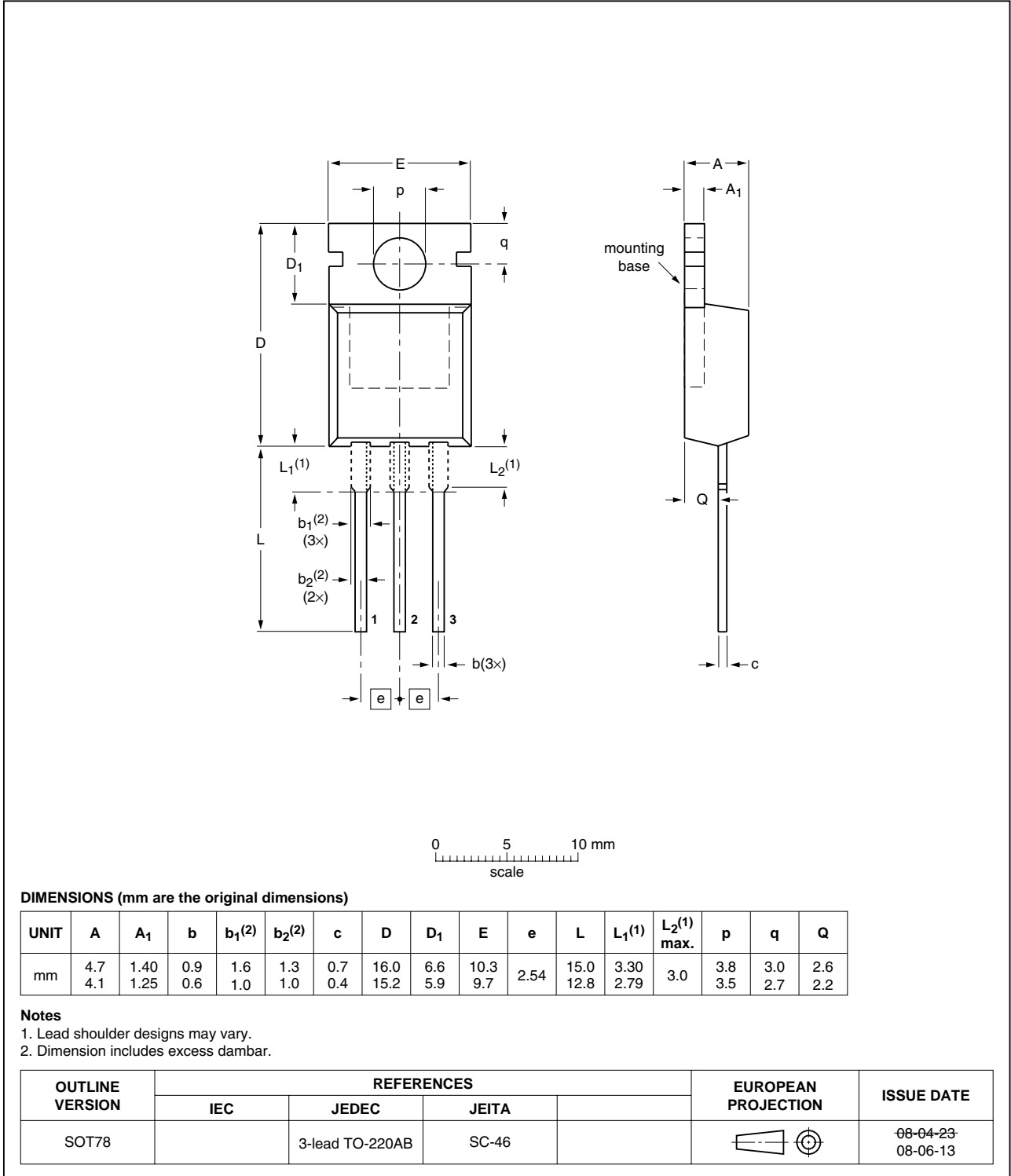


Fig 15. Package outline SOT78 (TO-220AB)

## 8. Revision history

Table 7. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
PHP3055E_7	20100226	Product data sheet	-	PHP_PHD3055E-06
Modifications:		<ul style="list-style-type: none"><li>• The format of this data sheet has been redesigned to comply with the new identity guidelines of NXP Semiconductors.</li><li>• Legal texts have been adapted to the new company name where appropriate.</li><li>• Typenumber PHP3055E separated from datasheet PHP_PHD3055E-06.</li></ul>		
PHP_PHD3055E-06 (9397 750 09354)	20020325	Product data	-	-

## 9. Legal information

### 9.1 Data sheet status

Document status <sup>[1][2]</sup>	Product status <sup>[3]</sup>	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

[1] Please consult the most recently issued document before initiating or completing a design.

[2] The term 'short data sheet' is explained in section "Definitions".

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